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Dissipative dynamics of spins in quantum dots

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We present a theory for the dissipation of electronic spins trapped in quantum dots due to their coupling to the host lattice acoustic phonon modes. Based on the theory of dissipative two level systems for the spin dynamics, we derive a relation between the spin dissipative bath, the electron confinement, and the electron-phonon interaction. We find that there is an energy scale, typically smaller than the electronic lateral confinement energy, which sets the boundary between different dissipative regimes .

Manipulating quantum states of matter to achieve new ways of processing information has been a subject of intense research in the last decade [1]. There is now a wide variety of proposals to take advantage of the internal transformations of quantum systems to perform the so-called quantum information processing (QIP) [2]. In particular, condensed matter systems such as SQUIDS and semiconductor quantum dots are seen as possible candidates for future implementations of QIP devices. In these systems, it is possible to find or create well defined two-level quantum states that potentially fulfill the minima criteria proposed by Di Vicenzo to be quantum bits (qubits) [3]. However, apart from the technical difficulties to implement acceptable qubits, nature imposes another limitation which is ubiquitous. This comes from the impossibility of perfectly isolating a complex quantum system from its environment that results in the loss of quantum coherence [4, 5].

In this paper we investigate the decoherence of electronic spins in quantum dots due to their coupling to the acoustic phonon modes of the host lattice. In few-electron quantum dots the electronic spin is a good candidate for a qubit and the confinement of the electronic wave function plays a major role in isolating the spins from most energy relaxation channels. In fact, using a second order perturbation approach, Khaetskii and Nazarov [6] have evaluated the spin-flip transition rate between Zeeman sublevels due to its coupling to acoustic phonons. They showed that, since angular momentum conservation requires the spin-flip process to involve a virtual transition between excited orbital states, the spin-flip rates are suppressed as ω_0^4, where ω_0 is the lateral confinement energy. According to their result, even for $\omega_0 \sim 1\,\mathrm{meV}$, the spin-flip rates can be of the order of milliseconds.

Quantum dots can be fabricated by confining a two dimensional electron gas of a semiconductor heterostructure into a region of the order of the Fermi wavelength. In the "lateral quantum dots" (LQD) this confinement is done laterally, by means of surface electrostatic metallic gates. In "vertical quantum dots" (VQD) the electron gas is confined vertically by etching techniques that create a circular pillar heterostructure. The typical lateral confinement length achieved with these fabrication techniques are of the order of hundreds of nanometers, which leads to $\omega_0 \sim 1\,\mathrm{meV}$ for LQD [7] and $\omega_0 \sim 3.5\,\mathrm{meV}$ for the VQD [8]. Much higher confinement energies can be achieved in self-assembled quantum dots (SAQD) which consist of ensembles of dislocation free semiconductor nano-crystals embedded into a semiconducting matrix of different band gap [9]. For InAs:GaAs SAQD [10] the electronic wave function extent is of the order of $50\,\text{Å}$, resulting in $\omega_0 \sim 50\,\mathrm{meV}$. For all the above systems single electron charging is easily observable due to their large Coulomb blockade gap, which can be of the order of $2\,\mathrm{meV}$ for LQD and VQD and as large as $20\,\mathrm{meV}$ for SAQD.

Although no experiment has so far been able to determine directly the decoherence rate, $\frac{1}{T_2}$, of spins in quantum dots, there are several attempts to indirectly determine lower bounds to the spin relaxation rate $\frac{1}{T_1}$. Paillard and co-workers [11] have studied the time-resolved photoluminescence of InAs:GaAs SAQD and observed that, within the time scale of an exciton lifetime, the carrier spins are totally frozen. Fujisawa and co-workers [8] have demonstrated that orbital sublevel transitions of VQD involving spin-flips have relaxation times that are 4 to 5 orders of magnitude longer than those which do not involve spin-flips. This gives an idea of the degree of isolation of the spins in the VQD. More recently, Hanson and co-workers [7] used short voltage pulse sequences to measure the relaxation time of spins in LQD and concluded that the lower bound of T_1 is $50\ \mathrm{s}$ for a magnetic field of $7.5\,\mathrm{T}$.

In quantum dots, the most important channels of dissipation for the spin are indirect and via the spin-orbit interaction. The orbital dissipative dynamics on its turn is dominated by the electron-phonon interactions. It is thus desirable to have a theoretical description which can connect the spin and orbital dissipation channels. A similar problem of indirect dissipation appears on a completely different context of electron tunneling between

the atoms of a diatomic molecule embedded in a viscous environment [12]. Here we analyze the spin dissipation in a quantum dot from the same perspective. We derive an effective "bath" spectral density seen by the spins that results from the spin-orbit coupling and the orbital damping.

Following previous theoretical works we treat the electrons in the effective mass approximation and consider the confining potential for the envelope wave function as parabolic. This was shown [13] to be a good approximation for the LQD and VQD with low electronic filling. Also, for SAQD this phenomenological model describes the orbital electronic density of states probed by magneto-capacitance measurements with fine accuracy up to the 3th excited level of the dot [10]. We further assume that the harmonic frequency in the direction perpendicular to the quantum dot plane, $!_?$, is much higher than the lateral harmonic frequency $!_0$. Therefore the relevant low energy orbital degrees of freedom are in the x y plane whereas the orbital dynamics in the z direction is practically frozen. This is a reasonable assumption even for typical InAs:GaAs SAQD since $\frac{!_?}{!_0}$ 8 10 [10]. For the spin degrees of freedom, besides the Zeeman term arising from an external magnetic field in the z direction, we include the Dresselhaus spin-orbit interaction projected on the $x;y$ plane [14] which is responsible for the coupling between the spins and the dissipative phonon bath. Thus, apart from a zero point energy on the z direction, the spin-orbit Hamiltonian will be

$$H_{SO} = \frac{}{2} {}_z + !_0 \; a_x^y a_x + \frac{1}{2} \; {}_x P_x + !_0 \; a_y^y a_y + \frac{1}{2} \; + \; {}_y P_y \qquad (1)$$

where $= g \; {}_B B_z$ (we use $\sim = 1$), ${}_c k_z^2 = {}_c m \; !_?$ (with ${}_c$ being the Kane parameter [14]), m is the electron effective mass and g its gyromagnetic factor. The operators $a_{x(y)}$ are the usual ladder operator for the x (y) direction. Notice that although we set an external field for the spins, we are neglecting any diamagnetic contribution for the orbital degrees of freedom like in the Fock-Darwin description. This simplification allows us to separate the degrees of freedom in the x and y directions and can be well justified for $!_0$ $\frac{!_c}{2}$, where $!_c = eB = (m \; c)$. One should also notice that, as opposed to the notation on reference [5], here plays the role of a "tunneling" field rather than the "bias" field, even though it refers to the z direction. This happens because dissipation occurs only in the x y plane of the dot.

The electron-phonon coupling in this restricted subspace can be written as

$$H_{e\,ph} = \sum_{q;} \; !_{q;} \; b_{q;}^y \; b_{q;} + \frac{C_{q;}}{\sqrt{V}} e^{iq:r} \; b_{q;}^y + b_{q;} \qquad (2)$$

where $C_{q;}$ is the electron-phonon coupling for phonons with polarization and frequency $!_{q;}$, and $r = (x;y;z)$ is the electron position operator. Here we consider only the piezoelectric and deformation potential interactions with acoustic phonon modes in zinc-blende structures [15]. It can be shown that within the linear response approximation for the phonon system the electron-phonon Hamiltonian (Eq.2) is mapped into the *bath of oscillators* model [4] with the spectral function given by

$$J_s (!) = m \; !_D^{2 \; s} \; \frac{!}{!_D}^{s} \; (!_D \; !) ;$$

where $s = 3$ for the piezoelectric interaction, with dimensionless coupling ${}_3 = \frac{(e_m)_{14}^2 !_D}{35 \; m} \; \frac{4}{3v_t^5} + \frac{1}{v_l^5}$, and $s = 5$ for the deformation potential, with ${}_5 = \frac{a_c^2 \; !_D^3}{2 \; m \; v_l^7}$, where $!_D$ is the Debye frequency, v_l and v_t are the longitudinal and transverse sound velocities respectively, is the material density, $(e_m)_{14}$ is the electromechanical tensor for zinc-blende structures [15], and $a_{c;}$ is the deformation potential in the point [15]. is the Heaviside step function.

Now, since the spin degree of freedom is coupled to the orbital motion of the electron, we can adopt the prescription of reference [12] to extract the spectral function of the effective heat bath to which the spin is now coupled. As opposed to the case of reference [12] where both the "spin" and the phonon degrees of freedom are coupled to the position of the orbit, here we have the phonon coupled to the position (Eq.2) and the spin to the momentum of the electron (Eq.1). This leads to a significant change on the "effective bath" spectral function, namely

$$J_{eff} (!) = m \; {}^2 \frac{{}_s \; \frac{!}{!_D}^{s+2}}{Z \; (!)^2 + {}_s^2 \; \frac{!}{!_D}^{2s}} \; (!_D \; !); \qquad (3)$$

where $Z \; (!) \; \frac{!_0}{!_D}^2 \; \frac{!}{!_D}^2 \; 1 + {}_s \; {}_s \; \frac{!}{!_D}$, and ${}_s (x) \; \frac{2}{} P \int_0^{R_1} x^s = y^3 \; yx^2 \; dy = \frac{x^{s\,2}}{} (B (x;s;0) + (\;1)^s B (\;x;s;0))$, with B being the generalized incomplete *beta function*. For x 1 we can approximate ${}_s (x) \; ' \; \frac{2}{} \; \frac{1}{s\,2} + \frac{x^2}{s\,4}$

For most semiconductors used in the fabrication of quantum dots the dimensionless constants ${}_3$ and ${}_5$ are of the order of 10^2 and 10^6 respectively. For instance, using the bulk physical paramenters [15] we obtain, in GaAs ${}_3 = 355$ and ${}_5 = 1{:}95 \; 10^6$ and in InAs ${}_3 = 149$ and ${}_5 = 5{:}03 \; 10^6$. Furthermore, the typical frequency for the spin dynamics is much smaller than $!_D$ 30 50 meV, which suggests an asymptotic analysis of $J_{eff} (!)$. In order to do that we should first notice that $J_{eff} (!)$, Eq. 3, is peaked at $! = {}_s$, where ${}_s$ is defined as the solution of $Z \; ({}_s) = 0$. For $!_0 \; . \; !_D$ this

solution is given by:

$$_s \quad !_0 \quad \frac{s}{(s \quad 2) + \frac{2 \ _s}{(s \quad 2)}} :$$

In the weak coupling limit, i.e., $_s \quad 1$, $_s \quad !_0 \ 1 \quad \frac{_s}{(s \ 2)}$ and the resonance at $_s$ corresponds to the harmonic frequency of the orbital dynamics, shifted by the electron-phonon coupling. However, for $_s \quad 1$, the peak originally centered at the lateral confinement frequency, $!_0$, is drastically shifted to $_s = !_0 \ \sqrt{\frac{(s \ 2)}{2 \ _s}}$. In the low frequency range, defined by $! \quad _s$ and $\frac{!}{!_D} \quad \frac{!_0}{!_D} \frac{1}{_s}^{1=s}$, we obtain

$$J_{eff} (!) \quad m^{2} \ _s \ \frac{!_D}{!_0}^{4} \ \frac{!}{!_D}^{s+2} : \qquad (4)$$

Note that in this limit the effective spectral function felt by the spins is always super-ohmic, with a power $s + 2$. On the other hand, in the high frequency limit, $_s \quad ! \quad !_D$, the spectral function can be approximated by

$$J_{eff} (!) \quad m^{2} \frac{^2 (s \quad 2)^2}{4 \ _s} \ \frac{!}{!_D}^{s \ 2} : \qquad (5)$$

In this limit the spectral function has a power $s \quad 2$ that can even be sub-ohmic. The behavior of $J_{eff} (!)$ is sketched in figure 1 for the piezoelectric interaction ($s = 3$).

All this complex structure of the effective spectral function will provide us with a new physics for the system. Within the adiabatic renormalization scheme, the fast modes of the bath, i.e. those with frequency much higher than , can quickly adjust to the spin flip motion and are successively integrated out by a Born-Oppenheimer approximation [5].

At long times the spins flips coherently with a renormalized Zeeman frequency $_r$, dressed by a Franck-Condon (FC) factor, which represents the polarization cloud of the high frequency phonon-orbit complex, given by :

$$_r = \ e^{F_s(_r)} ; \qquad (6)$$

where $F (z) = \frac{1}{2} \int_{pz}^{R_1} d! \frac{J_{eff}(!)}{!^2} \coth \frac{!}{2T}$ is the FC factor [5] with p being an unimportant dimensionless number much larger than 1. In the low frequency limit $z \quad _s$ the FC factor is dominated by the region $! \quad _s$ where $\frac{J_{eff}(!)}{!^2}$ can be well approximated by a Lorentzian of weight $\frac{1}{\mathbb{Z}^{0}(_s)\mathbb{j}}$ and width $_s = \frac{!_D \ _s \ _s}{\mathbb{Z}^{0}(_s)\mathbb{j}}$. For $_s \quad 1$, to the leading order in $_s^{1}$ we have $Z^{0}(_s) = 2\frac{!_D}{_s} \ \frac{!_0}{!_D}^{2}$ and thus $_s \ ' \ \frac{!_D \ (s \ 2)}{4} \ \frac{!_0}{!_D} \ \sqrt{\frac{(s \ 2)}{2 \ _s}} \quad _s \ 1$. Since $_r$, the solution for $_s$ involves integration over the entire spectrum of $J_{eff} (!)$, where most of the weight is concentrated around the peak centered at $_s$, and thus the lower limit of integration can be extended to zero, yielding

$$_r \quad \exp \ \frac{_s}{2T_0} \coth \frac{_s}{2T} \quad ;$$

where $T_0 = \frac{2!_0^2}{m \ ^2 n_0}$. For temperatures $T \quad _s$ we then have $_r \quad \exp \ \frac{T}{T_0}$. From this point onwards we restrict our discussion to the piezoelectric electron-phonon coupling which leads to a larger bath spectral density at low frequencies. In the low frequency limit, defined by $_3$, the dynamics is dominated by a super-ohmic relaxation with a power $s + 2$ (see Eq. 4). This allows the spin to present coherent damped oscillations with a decoherence rate [5] $\frac{1}{T_2} = 2J_{eff} (_r) \coth \frac{_r}{2T}$, given by

$$\frac{1}{T_2} \quad 2m^{2} \ _3 \ \frac{!_D}{!_0}^{4} \ \frac{_r}{!_D}^{5} \coth \frac{_r}{2T} :$$

Except for the renormalized Zeeman frequency $_r$, this is essentially the spin-flip rate from Khaetskii and Nazarov [6] which, for GaAs quantum dots with $m^{2} \ O (eV) \quad 10^{9} s^{1}$, $!_0 = 1 meV$ and $= 0:025 meV$, gives decoherence times of the order of milliseconds . One should note however that, since $_3 \quad O (0:1 !_0)$, for Zeeman splittings in the range $0:1 \quad 1 meV$ the perturbative result is only applicable for dots with lateral confinement energies $!_0 \quad 1 meV$. This is usually the case then for SAQD, in which one can have $!_0 \ ' \ 50 meV$. For the LQD and VQD $!_0 \quad O (1 meV)$ and thus can go beyond this perturbative limit. For $_3$, the relaxation is dominated by the resonance of the spin with the orbit-plus-phonons composite at frequency $_3$. This resonance has a linewidth of $_3 \ ' \ \frac{!_0^2}{!_D} \ \frac{^2}{8 \ _s}$ which qual-

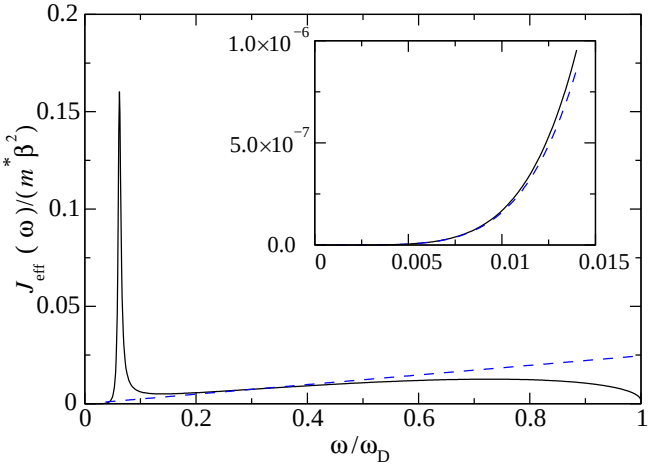


Figure 1: Full lines, exact $J_{eff} (!)$ ($s = 3$, $\frac{!_0}{!_D} = 0:5$ and $_3 = 100$), dashed lines, asymptotic behavior according to Eq. 5 and Eq. 4 (inset).

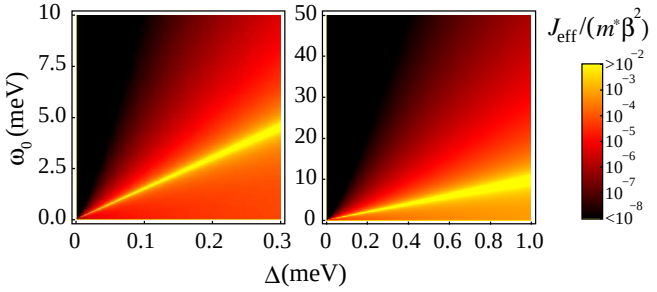


Figure 2: Density map of J_{eff}/m^{*2} from piezoelectric interaction ($s=3$) for GaAs (left) and InAs (right) QD.

itatively determines the decoherence rate of the spin in this intermediate range of frequencies.

In the higher frequency range $_s$ ω_D the integral on equation (6) is dominated by the high frequency part of $J_{eff}(\omega)$. For $s>3$ this integral is algebraic and only leads to a small correction. However, if s 3 the behavior is qualitatively different and dominated by the lower limit of the integration which has an "infrared divergence". For the piezoelectric interaction ($s=3$), it behaves at low temperatures T $_D$ as

$$\frac{_r}{\omega_D} = \frac{}{\omega_D}^{\frac{1}{1\ K}};$$

where $K = \frac{m^{*2}}{\omega_D}\frac{^2(s\ 2)^2}{8\ _s}$ 1: In this "high frequency region", $_s$ ω_D; that can be achieved for ω_0 1meV ("large" quantum dots), the decoherence will be dominated by an ohmic-like dissipation given by Eq. 5, which yields a decoherence rate

$$\frac{1}{T_2} \quad m^{*2}\frac{^2}{2\ _s}\quad\frac{_r}{\omega_D} \quad :$$

Figure 2 shows the behavior of J_{eff} for GaAs and InAs quantum dots. The darkest region to the left (right) of the brighter stripe (corresponding to the peak) is the super-ohmic (ohmic) dissipation. A perpendicular magnetic field will increase the lateral confinement according to the Fock-Darwin energy $\omega_{FD} = \sqrt{\omega_0^2 + \frac{1}{4}\omega_c^2}$. This is the case for the experiment on reference [7] where the magnetic fields are of the order of 10T and thus the cyclotron frequency ω_c contribution can be higher than ω_0. The density map of Figure 2 is then a guide for one to reach lowest decoherence rates given the lateral confinement energy of the dot and the Zeeman splitting .

Thus, we conclude that the piezoelectric electron-phonon coupling only leads to large decoherence times, as predicted by the second-order perturbation theory, if the $\frac{}{\omega_0}$ $\frac{p\overline{1}}{3}$. Otherwise the decoherence rate has a completely different behavior leading to much higher decoherence rates. This suggests that as far as the decoherence due to acoustic phonons is concerned, SAQD better decouple the electronic spin degree of freedom from the environment. Nevertheless one should note that there are other decoherence mechanisms due to phonons. In reference [16] other electron phonon mechanisms were considered extending the analysis of Khaetskii and Nazarov [6]. It has also been argued [17, 18, 19] that in SAQD, a resonance between the lateral confinement frequency and the longitudinal optical (LO) phonon mode can lead to a more efficient channel of orbital energy dissipation. In this scenario the orbital relaxation rate should be determined by the LO relaxation rate $_{op}$(in bulk GaAs $^1_{op}$ 7ps). Since the approach developed here connects the spin dissipation to the orbital dissipation and thus must also apply to these other orbital dissipation mechanisms if we replace $J(\omega)$ by the appropriate bath spectral function.

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